

AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the claims

Claim 1 (currently amended): A method for manufacturing a semiconductor laser device, comprising the steps of:

forming an electrode pattern patterns arranged in a plurality of rows extending in a first direction on an upper surface of a semiconductor wafer stacked having at least a light emission layer, the electrode patterns having opposed two edges extending in the first direction;

cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and

sectioning the semiconductor bars into a in desired size sizes to form semiconductor laser devices each having a pair of cleavage surfaces, which are the surfaces being parallel to a chip width second direction and distant from each other by a predetermined resonator length,

wherein the formed electrode pattern patterns formed in the step of forming an electrode pattern is are continuous at least with each other in a resonator length the first direction, each electrode pattern including a series of markers having a periodical pattern, the markers being formed at one or both of the edges of the electrode patterns, and a minimum unit of the periodical pattern has an overall length in the first direction equal to L/n and not reater than the resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, the second direction being perpendicular to the first direction.

Claims 2-4 (cancelled)

Claim 5 (original): A semiconductor laser device, comprising:
a semiconductor layer portion ~~which includes~~ including at least a light emission layer
and ~~has~~ a pair of cleavage surfaces ~~which are~~ the surfaces being parallel to a chip-width direction
and distant from each other by a predetermined resonator length; and

an electrode pattern piece formed on an upper surface of the semiconductor layer
portion, the electrode pattern piece having opposed two first edges extending in a first direction and
opposed two second edges extending in a second direction along the pair of cleavage surfaces.

wherein the two second edges come electrode pattern piece comes in contact with the
pair of cleavage planes surfaces at both of the edges of the electrode pattern piece extending in a
chip-width direction, each electrode pattern piece including a series of markers having a periodical
pattern formed at one or both of the first edges, a minimum unit of the periodical pattern having an
overall length in the resonator-length direction equal to L/n and not greater than a resonator length,
wherein L is the resonator length and n is a positive real number not smaller than one, the first
direction being a direction along the resonator length, wherein the markers can be used to form laser
chips of different resonator lengths.

Claims 6-9 (cancelled)

Claim 10 (currently amended): The device of ~~claim 5 claims 6 or 9~~, wherein the series of
markers marker is set are arranged so that the ratio of its the overall length of the semiconductor
laser device in the resonator-length direction to its maximum length in the chip-width direction is
1:5 to 5:1.

Claim 11. (New): The method of claim 1, wherein the semiconductor wafer is cut in
predetermined widths to yield a plurality of semiconductor bars extending in the resonator-length
direction, and the plurality of semiconductor bars are cut in predetermined resonator lengths.

Claim 12. (New): The method of claim 11, wherein one of the semiconductor bars is cut in
different resonator lengths to yield a plurality of different semiconductor laser devices.

Claim 13. (New): The method of claim 11, wherein one of the semiconductor bars is cut in integral multiple lengths of the overall length of the marker.

Claim 14. (New): The method of claim 5, wherein the series of markers are shaped like teeth of a saw.

Claim 15. (New): The method of claim 5, wherein one of the markers is formed in a shape of right triangle, equilateral triangle, isosceles triangle, semicircle or semiellipse.